Analog Power AM2341P

## P - Channel 40V (D-S) MOSFET

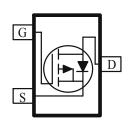
These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are lower voltage application, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

$0.082 \ \text{@V}_{GS} = -10 \ \text{V}$ -3.2	1 11300	OT GOWNANT			
$0.082 @ V_{GS} = -10 V$ -3.2	V <sub>DS</sub> (V)	$r_{DS(on)}(\Omega)$	$I_{D}(A)$		
	-40	$0.082 @ V_{GS} = -10 V$	-3.2		
10	-40	$0.130 @ V_{GS} = -4.5V$	-2.6		

PRODUCT SUMMARY

- Low r<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Fast Switch
- Low Gate Charge
- Miniature SOT-23 Surface Mount Package Saves Board Space

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ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Ratings	Units	
Drain-Source Voltage			-40	$\mathbf{V}$	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continues Durin Connect <sup>a</sup>	$T_A=25^{\circ}C$	Τ_	± 3.2		
Continuous Drain Current <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	П	± 2.7	A	
Pulsed Drain Current <sup>b</sup>			±10		
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	0.4	A	
D a	$T_A=25^{\circ}C$	D	1.25	W	
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$		0.8	**	
Operating Junction and Storage Temperature Range		$T_{J}, T_{stg}$	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
M · I · · · · · · · · · · · · · · · · ·	t <= 5 sec	D	100	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	$R_{THJA}$	150	C/W		

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

D	G 1	T	Limits			<b>T</b> T •.
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Switch Off Characteristics						
Zara Cata Valtaga Drain Current	IDSS	$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μА
Zero Gate Voltage Drain Current		$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	
Gate-Body Leakage	Igss	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \text{ uA}$	-1.0			V
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{\rm DS}$ = -5 V, $V_{\rm GS}$ = -4.5 V	-2			A
D : G O D : A	fDS(on)	$V_{GS} = -10 \text{ V}, I_D = -3.2 \text{ A}$			82	mΩ
Drain-Source On-Resistance <sup>A</sup>		$V_{GS} = -4.5 \text{ V}, I_D = -2.6 \text{ A}$			130	
Forward Tranconductance <sup>A</sup>	gs	$V_{DS} = -5 \text{ V}, I_D = -3.6 \text{ A}$		2		S
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = -0.4 \text{ A}, V_{GS} = 0 \text{ V}$		-0.70		V
Dynamic <sup>b</sup>						
Total Gate Charge	Qg	Vos = 10 V Vos = 5 V		15		
Gate-Source Charge	Qgs	$V_{DS} = -10 \text{ V}, V_{GS} = -5 \text{ V},$ $I_{D} = -3.6 \text{ A}$		2.0		nC
Gate-Drain Charge	Qgd	1D = -3.0  A		2.0		
Turn-On Delay Time	td(on)			10		
Rise Time	$t_{\rm r}$	$V_{DS} = -15 \text{ V}, I_D = -1 \text{ A},$		2.8		ns
Turn-Off Delay Time	td(off)	$R_G = 50 \Omega$ , $V_{GEN} = -10 V$		53.6		
Fall-Time	$t_{\mathrm{f}}$			46		

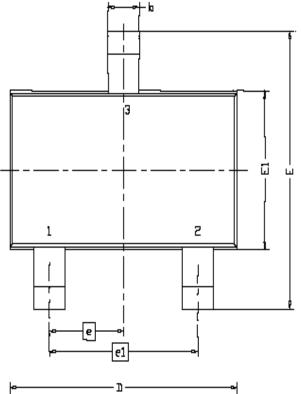
## Notes

- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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## Package Information



DIM.	MILLIMETERS			
יהודת	MIN NOM		MAX	
Α	0.935	0.95	1.10	
A1	0.01		0.10	
A2	0.85	0.90	0.925	
р	0.30	0.40	0.50	
С	0.10	0.15	0,25	
D	2.70	2.90	3.10	
П	2.60	2.80	3.00	
E1	1.40	1.60	1.80	
6	0.95 BSC			
el	1.90 BSC			
Г	0.30	0.40	0.60	
L1	0.60REF			
LZ	0.25BSC			
R	0.10			
θ	Q*	4*	8,	
01	7"N□M			

